

IN THE ABSTRACT OF THE DISCLOSURE:

Please amend the abstract of the disclosure as follows:

Abstract of the ~~Invention~~ Disclosure

~~The present invention relates to~~ In a method ~~for~~ of measuring a three dimensional shape of an arbitrary fine pattern on a semiconductor device. ~~An, an~~ optical measurement system ~~measures~~ carries out a measurement to obtain cross-section information. ~~An, and an~~ electron microscope obtains an electron beam image of the arbitrary fine pattern. Plane information and cross-section information obtained from the electron beam image of the arbitrary fine pattern are combined to measure the three dimensional shape of the arbitrary fine pattern.